

FEATURES

- Low Switching Losses At High Frequency
- Fully Characterised For Operation Up To 20kHz

APPLICATIONS

- High Power Inverters And Choppers
- UPS
- AC Motor Drives
- Induction Heating
- Cycloconverters

VOLTAGE RATINGS

| Type Number | Repetitive Peak Voltages V_{DRM} V_{RRM} V | Conditions |
|--------------------------------------|--|--|
| DK27 12FA K or M DK27 10FA K or M | 1200 1000 | $V_{RSM} = V_{RRM} + 100V$ $I_{DRM} = I_{RRM} = 25mA$ at V_{RRM} or V_{DRM} & T_{vj} |

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table, then:-

Add K to type number for 3/4" 16 UNF thread, e.g. **DK27 12FAK**
or

Add M to type number for M16 thread, e.g. **DK27 12FAM**.

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

| | |
|--------------|----------------|
| V_{DRM} | 1200V |
| $I_{T(RMS)}$ | 290A |
| I_{TSM} | 5000A |
| dV/dt | 200V/μs |
| dI/dt | 500A/μs |
| t_q | 20μs |

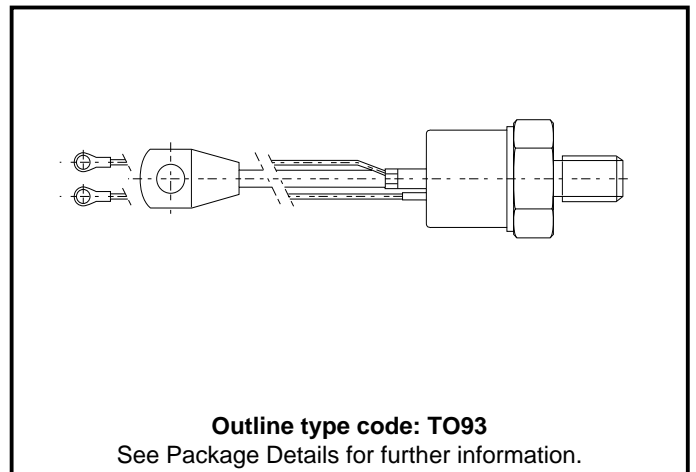


Fig. 1 Package outline

CURRENT RATINGS

| Symbol | Parameter | Conditions | Max. | Units |
|--------------|-----------------------|--|------|-------|
| $I_{T(AV)}$ | Mean on-state current | Half wave resistive load, $T_{case} = 80^{\circ}C$ | 185 | A |
| $I_{T(RMS)}$ | RMS value | $T_{case} = 80^{\circ}C$ | 290 | A |

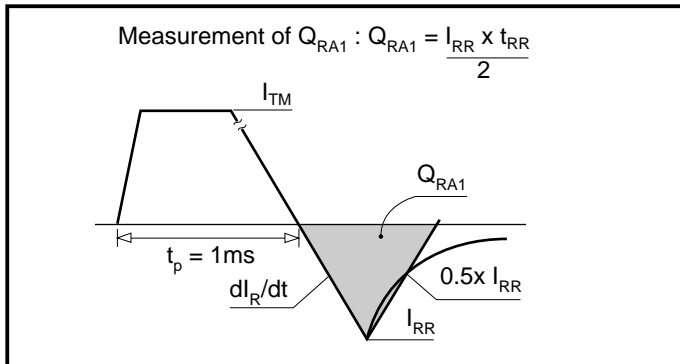
SURGE RATINGS

| Symbol | Parameter | Conditions | Max. | Units |
|-----------|---|--|---------------------|------------------|
| I_{TSM} | Surge (non-repetitive) on-state current | $t_p \geq 10ms$ half sine; $T_{case} = 125^{\circ}C$ $V_R = 0\% V_{RRM} - 1/4$ sine | 5.0 | kA |
| I^2t | I^2t for fusing | | 125.0×10^3 | A ² s |

THERMAL AND MECHANICAL DATA

| Symbol | Parameter | Conditions | Min. | Max. | Units |
|---------------|---------------------------------------|---|------|------|---------------|
| $R_{th(j-c)}$ | Thermal resistance - junction to case | dc | - | 0.13 | $^{\circ}C/W$ |
| $R_{th(c-h)}$ | Thermal resistance - case to heatsink | Mounting torque 35.0Nm with mounting compound | - | 0.06 | $^{\circ}C/W$ |
| T_{vj} | Virtual junction temperature | On-state (conducting) | - | 125 | $^{\circ}C$ |
| | | Reverse (blocking) | - | 125 | $^{\circ}C$ |
| T_{stg} | Storage temperature range | | -40 | 150 | $^{\circ}C$ |
| - | Mounting torque | | 30.0 | 35.0 | Nm |

MEASUREMENT OF RECOVERED CHARGE - Q_{RA1}



DYNAMIC CHARACTERISTICS

| Symbol | Parameter | Conditions | Min. | Max. | Units | |
|-------------------|--|---|-----------------|------|------------|------------|
| V_{TM} | Maximum on-state voltage | At 600A peak, $T_{case} = 25^{\circ}C$ | - | 1.85 | V | |
| I_{RRM}/I_{DRM} | Peak reverse and off-state current | At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$ | - | 25 | mA | |
| dV/dt | Maximum linear rate of rise of off-state voltage | Linear to 60% V_{DRM} , $T_j = 125^{\circ}C$, Gate open circuit | - | 200 | V/ μ s | |
| dI/dt | Rate of rise of on-state current | Gate source 20V, 20 Ω | Repetitive 50Hz | - | 500 | A/ μ s |
| | | $t_f < 0.5\mu$ s, $T_j = 125^{\circ}C$ | Non-repetitive | - | 800 | A/ μ s |
| $V_{T(To)}$ | Threshold voltage | At $T_{vj} = 125^{\circ}C$ | - | 1.2 | V | |
| r_T | On-state slope resistance | At $T_{vj} = 125^{\circ}C$ | - | 1.0 | m Ω | |
| t_{gd} | Delay time | $T_j = 25^{\circ}C$, $I_T = 50A$, $V_D = 300V$, $I_G = 1A$, $dI/dt = 30A/\mu$ s, $dI_G/dt = 1A/\mu$ s | 1.5* | - | μ s | |
| $t_{(ON)TOT}$ | Total turn-on time | | 3* | - | μ s | |
| I_H | Holding current | $T_j = 25^{\circ}C$, $I_{TM} = 1A$, $V_D = 12V$ | - | 70 | mA | |
| t_q | Turn-off time | $T_j = 125^{\circ}C$, $I_T = 200A$, $V_R = 50V$, $dV/dt = 200V/\mu$ s (Linear to 60% V_{DRM}), $dI_R/dt = 30A/\mu$ s, Gate open circuit | t_q code: A | - | 20 | μ s |

*Typical value.

GATE TRIGGER CHARACTERISTICS AND RATINGS

| Symbol | Parameter | Conditions | Typ. | Max. | Units |
|-------------|---------------------------|--|------|------|-------|
| V_{GT} | Gate trigger voltage | $V_{DRM} = 12V$, $T_{case} = 25^{\circ}C$, $R_L = 6\Omega$ | - | 3.0 | V |
| I_{GT} | Gate trigger current | $V_{DRM} = 12V$, $T_{case} = 25^{\circ}C$, $R_L = 6\Omega$ | - | 200 | mA |
| V_{GD} | Gate non-trigger voltage | At V_{DRM} , $T_{case} = 125^{\circ}C$, $R_L = 1k\Omega$ | - | 0.2 | V |
| V_{RGM} | Peak reverse gate voltage | | - | 5.0 | V |
| I_{FGM} | Peak forward gate current | Anode positive with respect to cathode | - | 4 | A |
| P_{GM} | Peak gate power | | - | 16 | W |
| $P_{G(AV)}$ | Mean gate power | | - | 3.0 | W |

CURVES

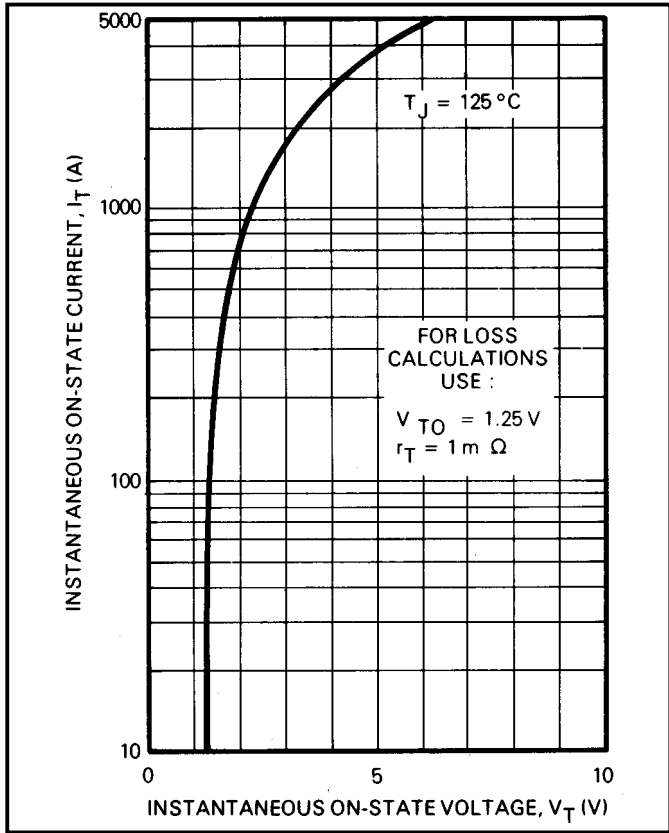


Fig.2 Maximum (limit) on-state characteristics

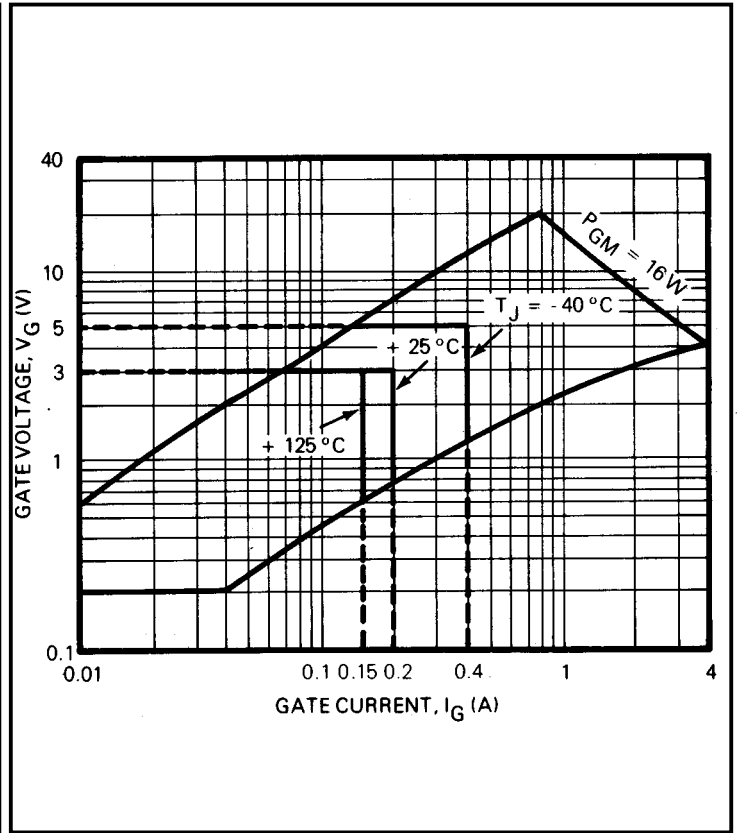


Fig.3 Gate characteristics

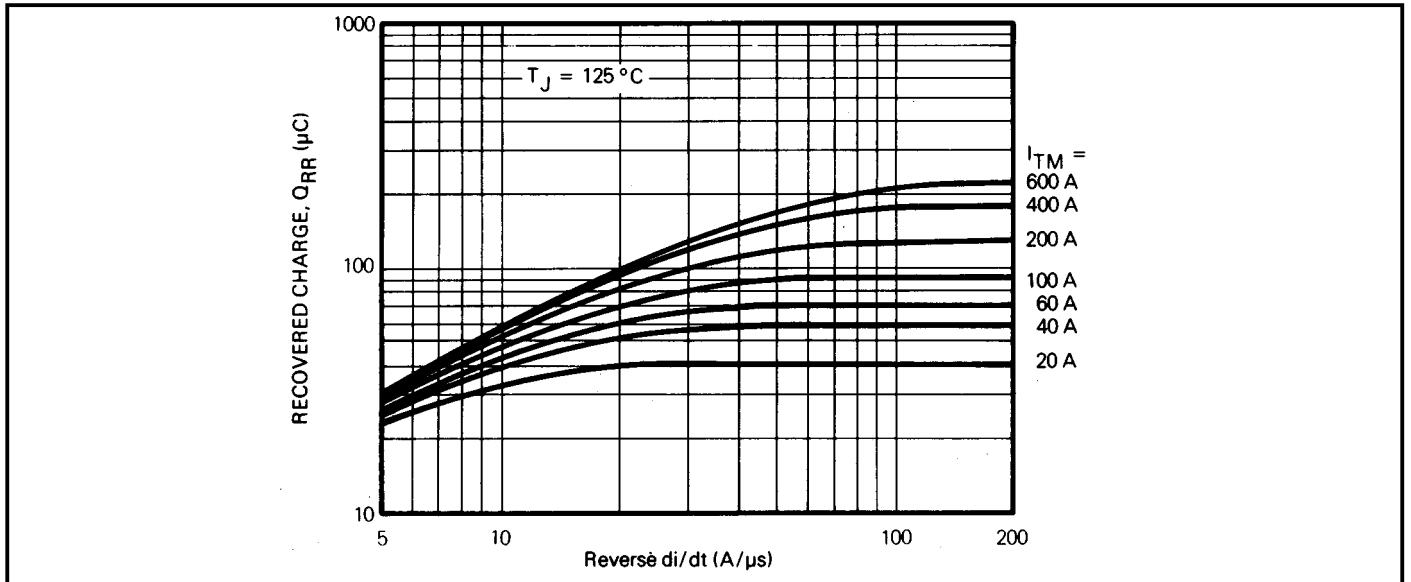


Fig.4 Typical recovered charge (for a device rated $V_{DRM} = 800\text{ V}$, $t_q = 20\mu\text{s}$)

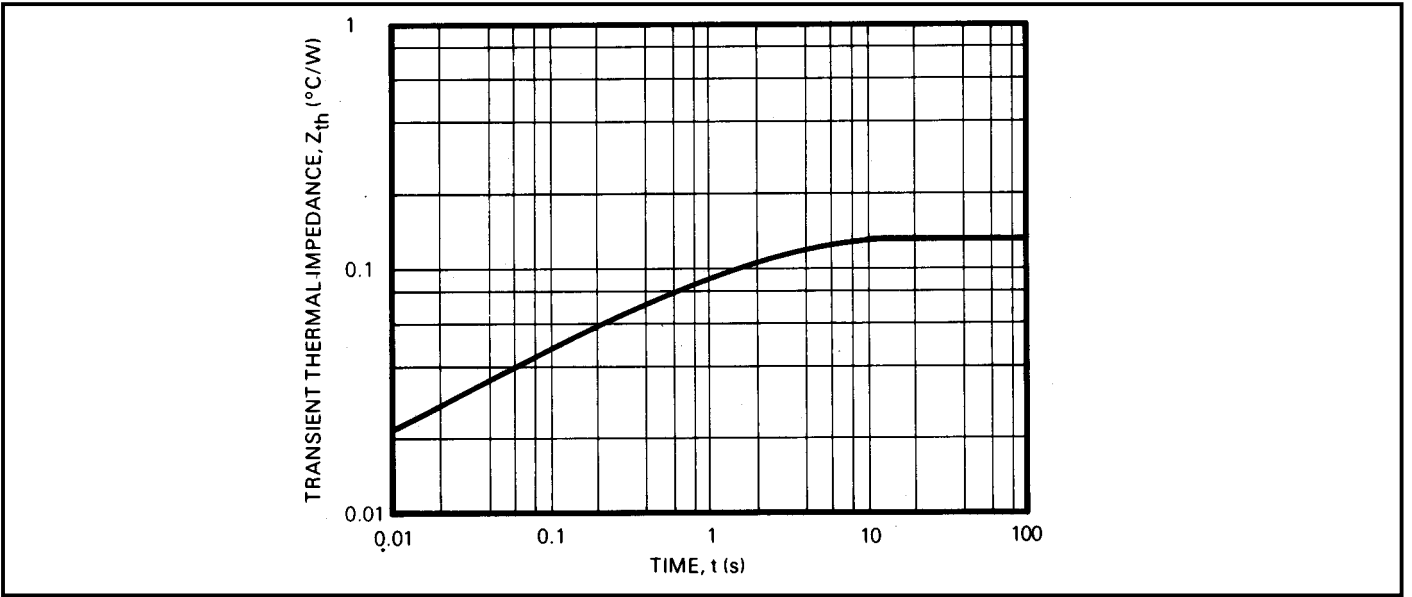


Fig.5 Transient thermal impedance - junction to case

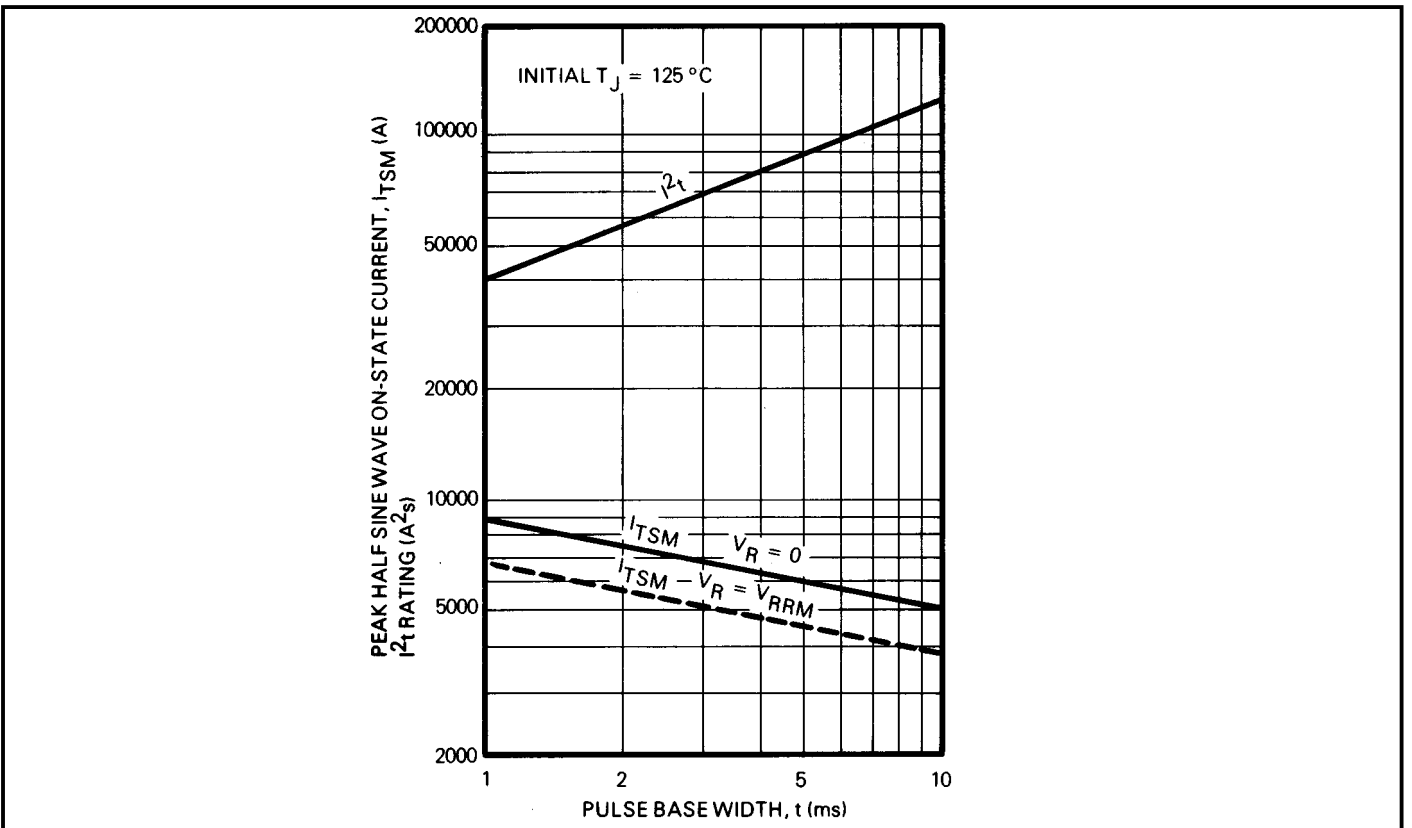


Fig.6 Non-repetitive sub-cycle surge on-state current and I^2t rating

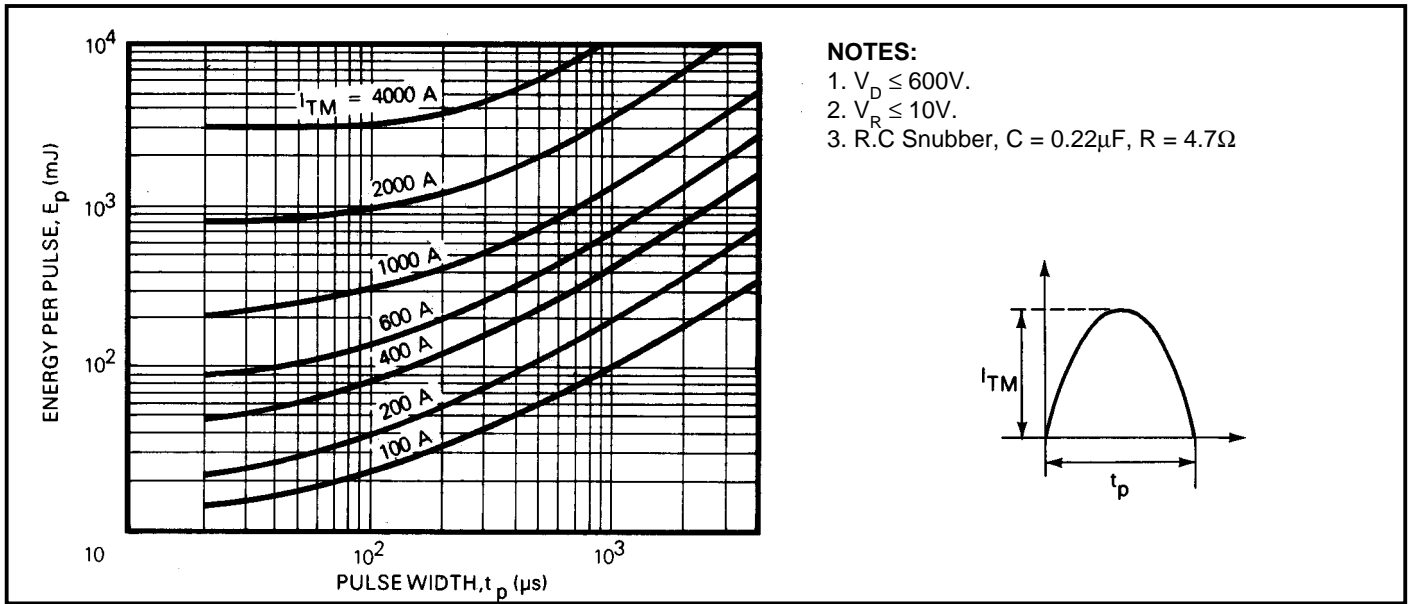


Fig.7 Energy per pulse for sinusoidal pulses

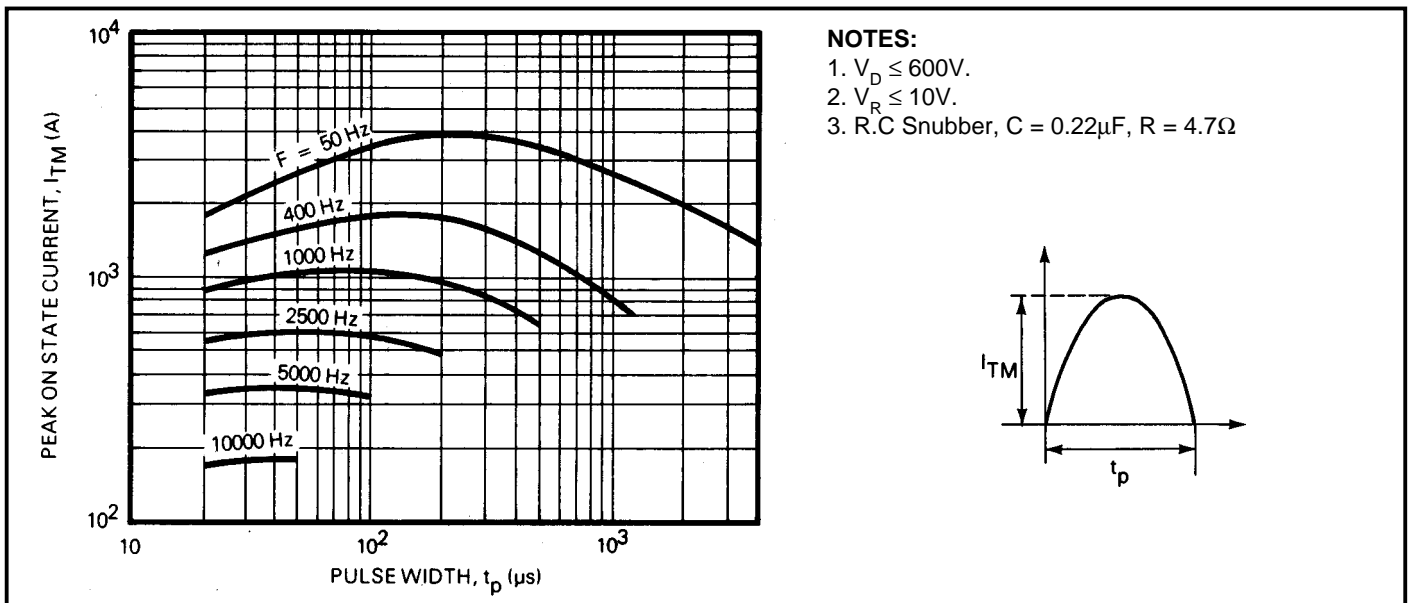


Fig.8 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ C$

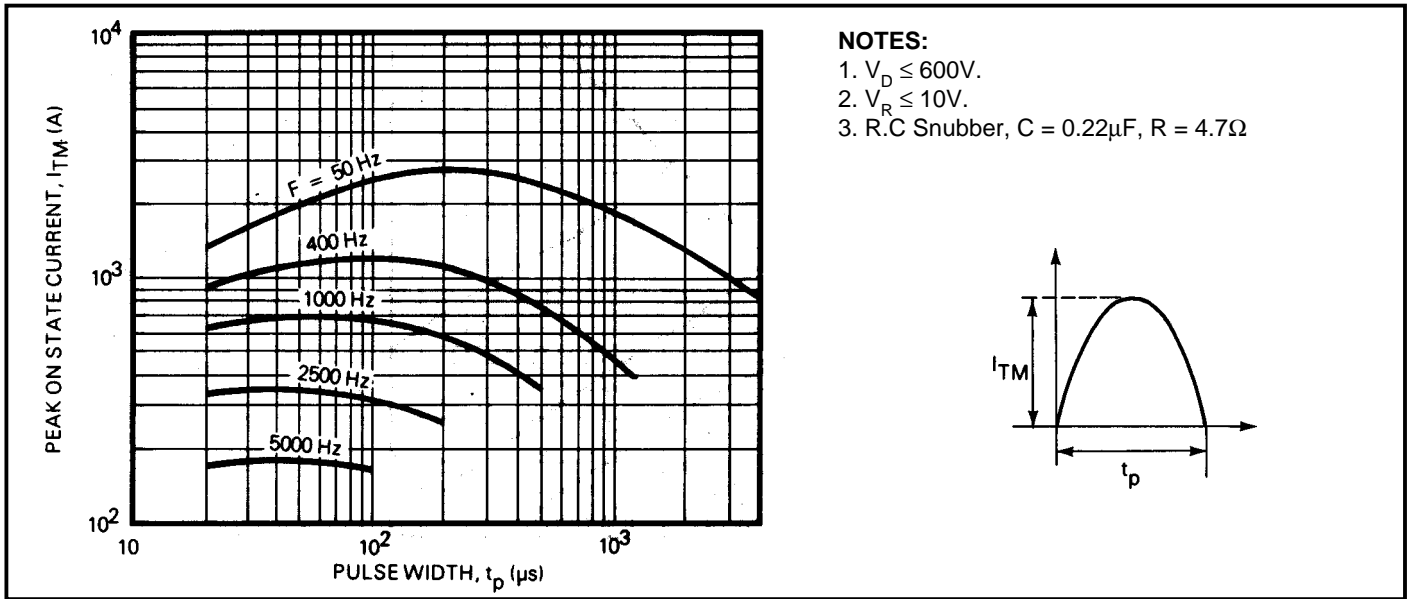


Fig.9 Maximum allowable peak on-state current vs pulse width for $T_{case} = 90^\circ C$

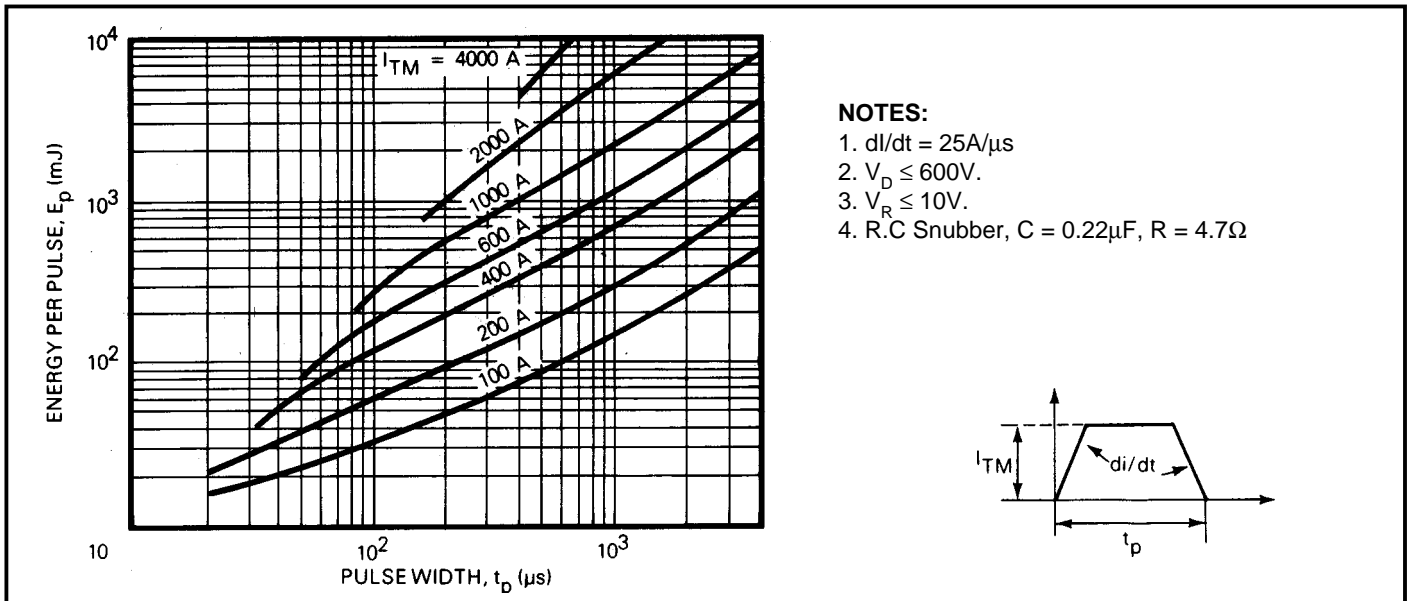
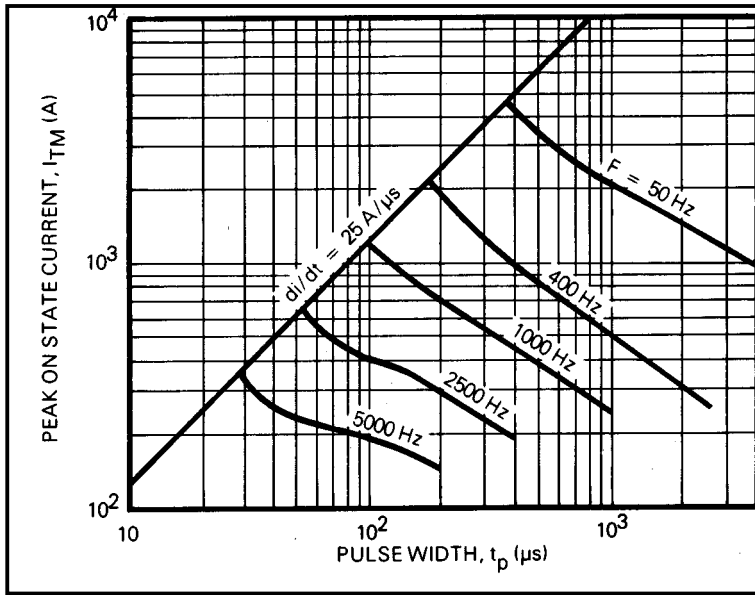


Fig.10 Energy per pulse for trapezoidal pulses



NOTES:

1. $di/dt = 25A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

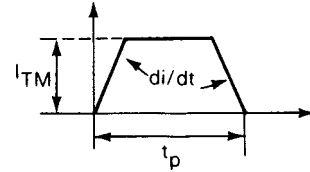
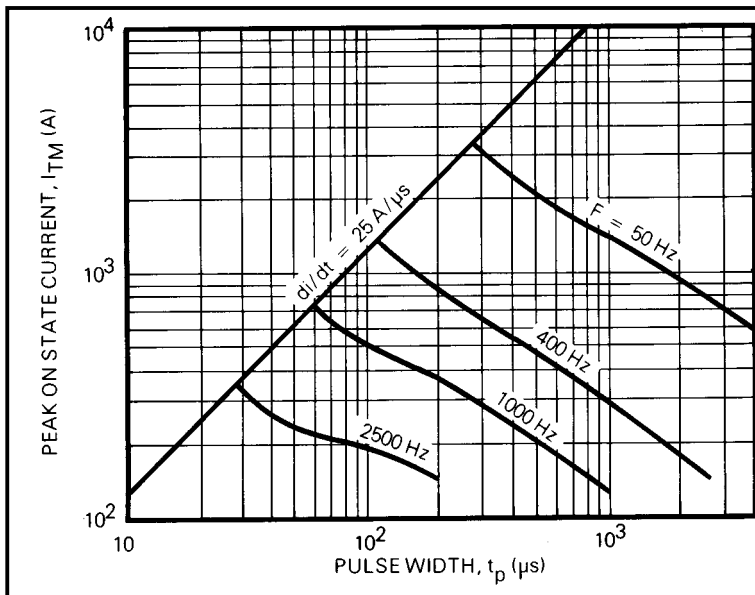


Fig.11 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ C$



NOTES:

1. $di/dt = 25A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

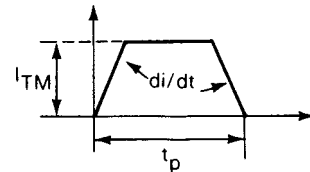
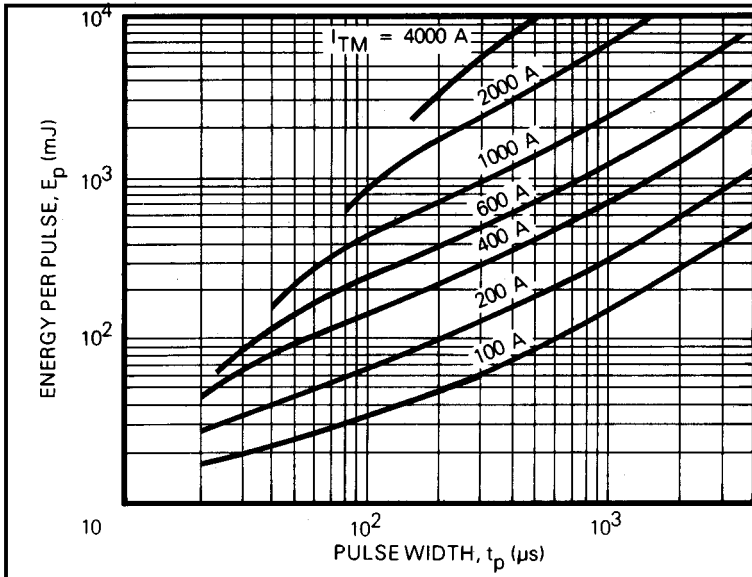


Fig.12 Maximum allowable peak on-state current vs pulse width for $T_{case} = 90^\circ C$



NOTES:

1. $di/dt = 50A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

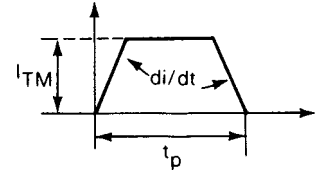
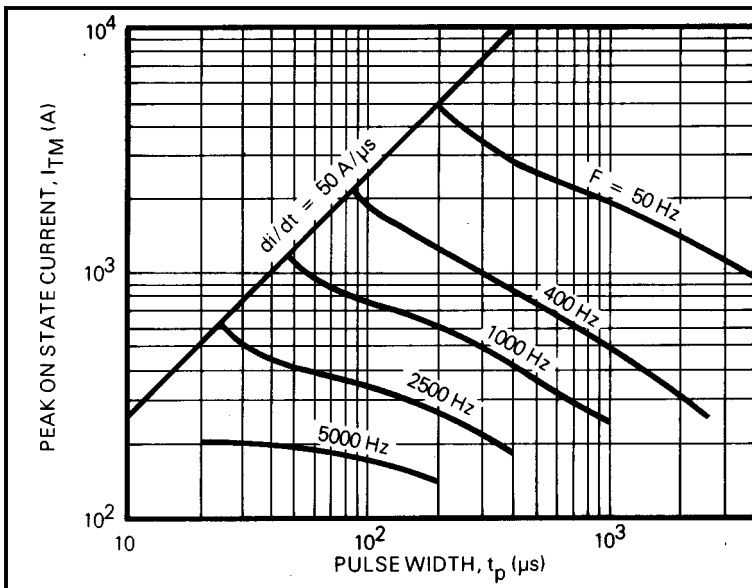


Fig.13 Energy per pulse for trapezoidal pulses



NOTES:

1. $di/dt = 50A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

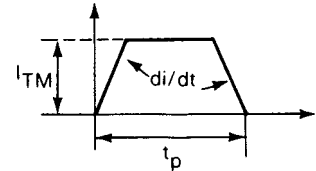
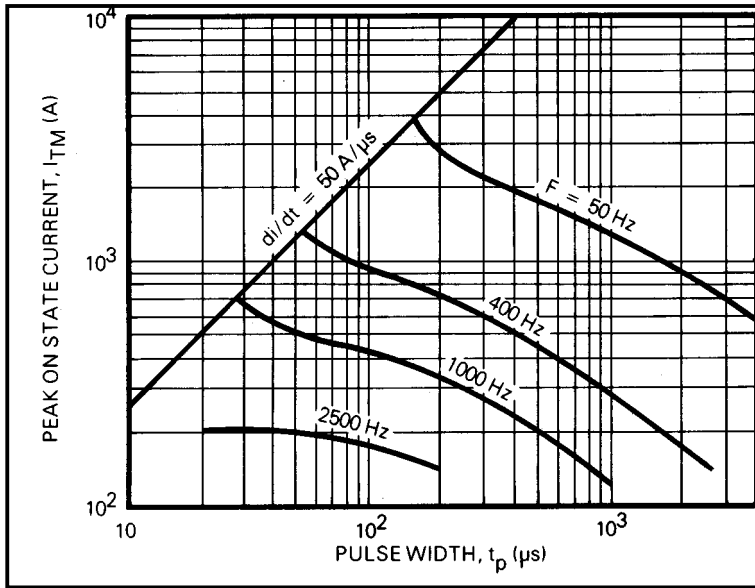


Fig.14 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ C$



NOTES:

1. $di/dt = 50 A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

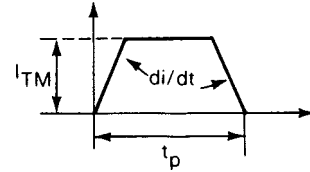
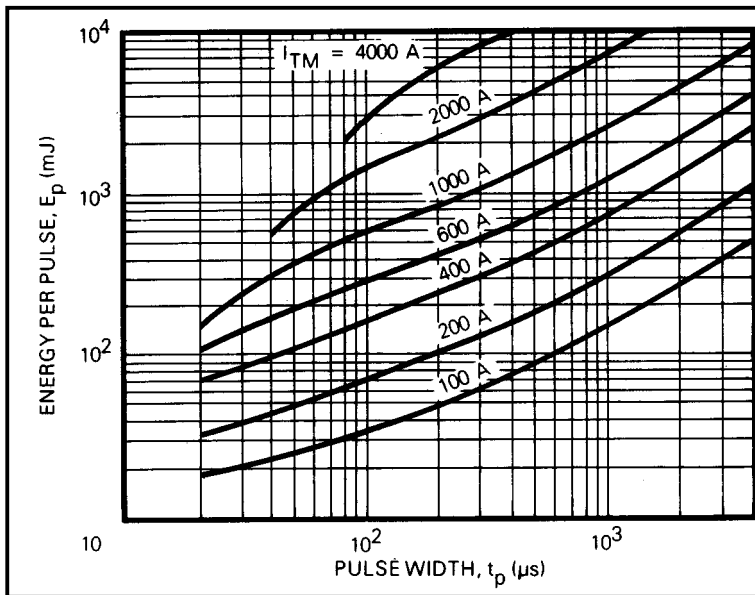


Fig.15 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ C$



NOTES:

1. $di/dt = 100A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

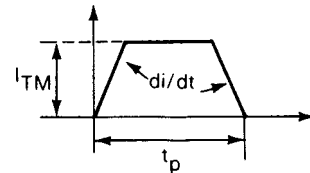
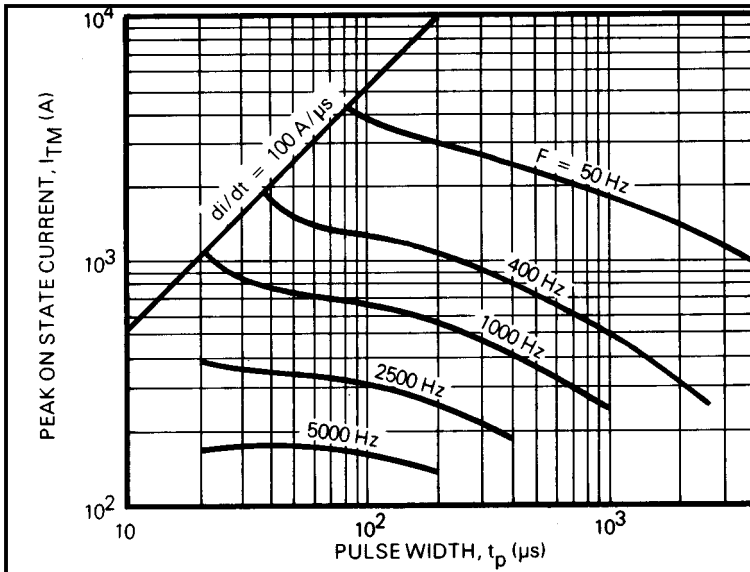


Fig.16 Energy per pulse for trapezoidal pulses



NOTES:

1. $di/dt = 100A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

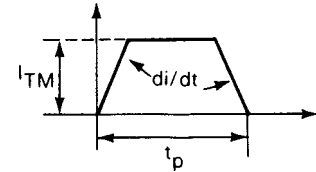
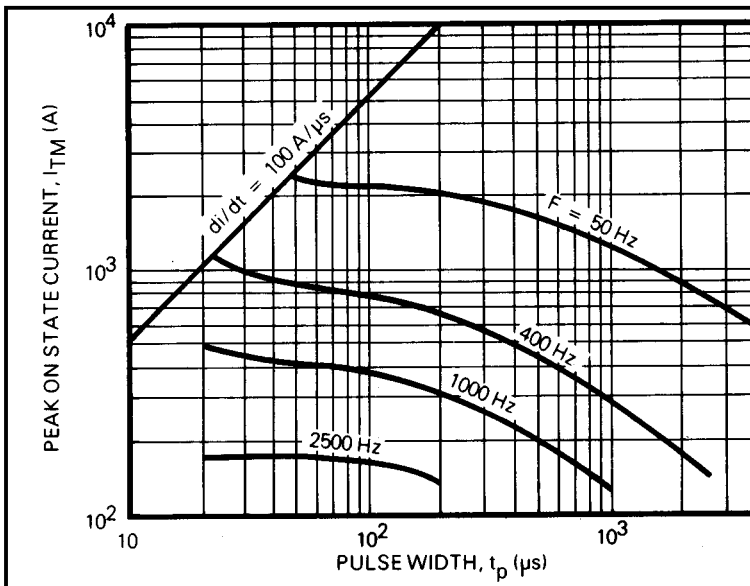


Fig.17 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ C$



NOTES:

1. $di/dt = 100A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

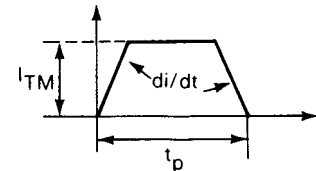
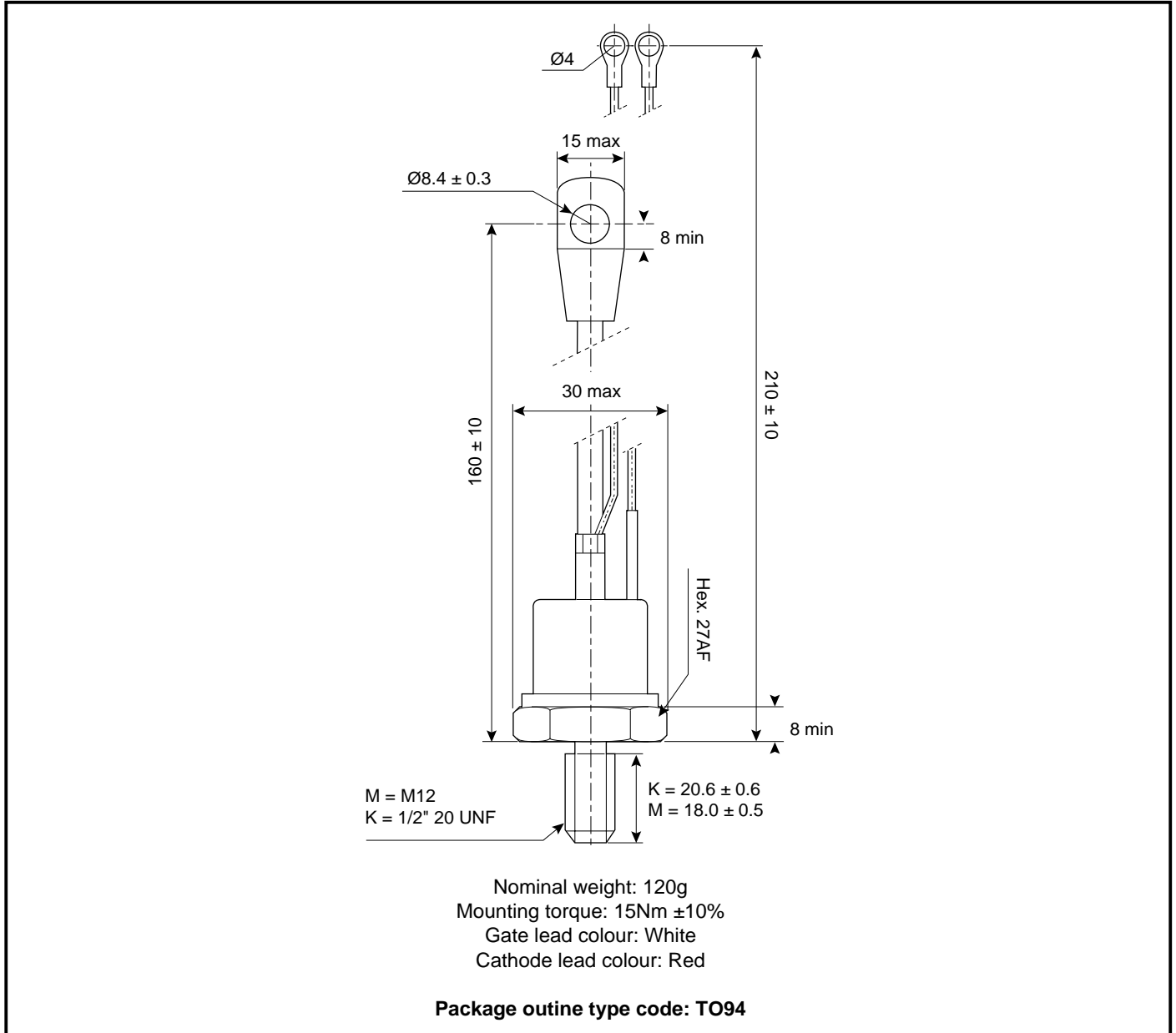


Fig.18 Maximum allowable peak on-state current vs pulse width for $T_{case} = 90^\circ C$

PACKAGE DETAILS

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

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No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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